Manh-Ha Doan

List of Publications by Year
in descending order

18 papers	639 citations	1039406 9 h-index	996533 15 g-index
19 all docs	19 docs citations	19 times ranked	1344 citing authors

#	Article	IF	Citations
1	Modulation of optoelectric properties of monolayer transition metal dichalcogenides placed on a metal pattern. Journal of the Korean Physical Society, 2021, 78, 693-699.	0.3	5
2	Super-Resolution Nanolithography of Two-Dimensional Materials by Anisotropic Etching. ACS Applied Materials & Interfaces, 2021, 13, 41886-41894.	4.0	16
3	Ultrashort Verticalâ€Channel van der Waals Semiconductor Transistors. Advanced Science, 2020, 7, 1902964.	5.6	24
4	Schottky-barrier quantum well in two-dimensional semiconductor nanotransistors. Materials Today Physics, 2020, 15, 100275.	2.9	4
5	Bandgap Renormalization in Monolayer MoS₂ on CsPbBr₃ Quantum Dots via Charge Transfer at Room Temperature. Advanced Materials Interfaces, 2020, 7, 2000835.	1.9	8
6	Ferromagnetic Order at Room Temperature in Monolayer WSe₂ Semiconductor via Vanadium Dopant. Advanced Science, 2020, 7, 1903076.	5.6	148
7	Roomâ€Temperature Mesoscopic Fluctuations and Coulomb Drag in Multilayer WSe₂. Advanced Materials, 2019, 31, e1900154.	11.1	12
8	Twoâ€Terminal Multibit Optical Memory via van der Waals Heterostructure. Advanced Materials, 2019, 31, e1807075.	11.1	168
9	Minimizing Trap Charge Density towards an Ideal Diode in Grapheneâ€“Silicon Schottky Solar Cell. ACS Applied Materials & Interfaces, 2019, 11, 880-888.	4.0	15
10	Role of Hole Trap Sites in MoS₂ for Inconsistency in Optical and Electrical Phenomena. ACS Applied Materials & Interfaces, 2018, 10, 10580-10586.	4.0	37
11	Facile Doping in Two-Dimensional Transition-Metal Dichalcogenides by UV Light. ACS Applied Materials & Interfaces, 2018, 10, 29893-29901.	4.0	18
12	Charge Transport in MoS₂/WSe₂ van der Waals Heterostructure with Tunable Inversion Layer. ACS Nano, 2017, 11, 3832-3840.	7.3	175
13	Spatially Resolved Cathodoluminescence in the Vicinity of Defects in the High-Efficiency InGaN/GaN Blue Light Emitting Diodes. Advances in Condensed Matter Physics, 2014, 2014, 1-5.	0.4	3
14	Nâ€GaN column arrays on the vertical InGaN/GaN blue LEDs formed by maskless dry etching. Crystal Research and Technology, 2014, 49, 116-121.	0.6	0
15	Enhanced Cathodoluminescence of KOH-treated InGaN/GaN LEDs with Deep Nano-Hole Arrays. Journal of the Optical Society of Korea, 2014, 18, 283-287.	0.6	0
16	Enhanced Cathodoluminescence from InGaN/GaN Light-emitting Diodes with Nanohole Arrays Fabricated Using Anodic Aluminum-oxide Masks. Journal of the Korean Physical Society, 2010, 57, 1295-1298.	0.3	2
17	Luminescence study of GaN-based vertical light emitting diodes. , 2010, , .		0
18	Cathode-luminescence study of photonic crystal green InxGa1â^'xN/InyGa1â^'yN light emitting diodes. Journal of Crystal Growth, 2009, 311, 863-866.	0.7	3